



Description

The SI7218DN-T1-E3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 30V$ $I_D = 24A$

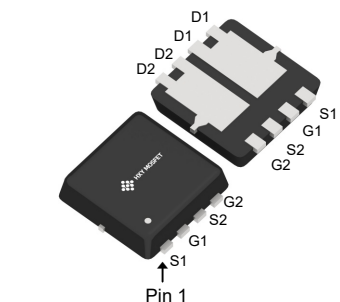
$R_{DS(ON)} < 18m\Omega$ @ $V_{GS}=10V$

Application

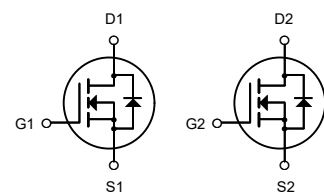
Lithium battery protection

Wireless impact

Mobile phone fast charging



DFN3X3B-8L
(PowerPAK1212-8)



Dual N-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SI7218DN-T1-E3	DFN3X3B-8L (PowerPAK1212-8)	HXY MOSFET	5000

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	30	V
VGS	Gate-Source Voltage	± 20	V
$I_{D@T_C=25^{\circ}C}$	Continuous Drain Current, V_{GS} @ 10V ¹	24	A
$I_{D@T_C=100^{\circ}C}$	Continuous Drain Current, V_{GS} @ 10V ¹	18	A
IDM	Pulsed Drain Current ²	56	A
EAS	Single Pulse Avalanche Energy ³	22.1	mJ
IAS	Avalanche Current	21	A
$P_{D@T_C=25^{\circ}C}$	Total Power Dissipation ⁴	20.8	W
$P_{D@T_A=25^{\circ}C}$	Total Power Dissipation ⁴	1.67	W
TSTG	Storage Temperature Range	-55 to 150	$^{\circ}C$
TJ	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$
R θ JA	Thermal Resistance Junction-Ambient ¹	75	$^{\circ}C/W$
R θ JC	Thermal Resistance Junction-Case ¹	6	$^{\circ}C/W$



Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

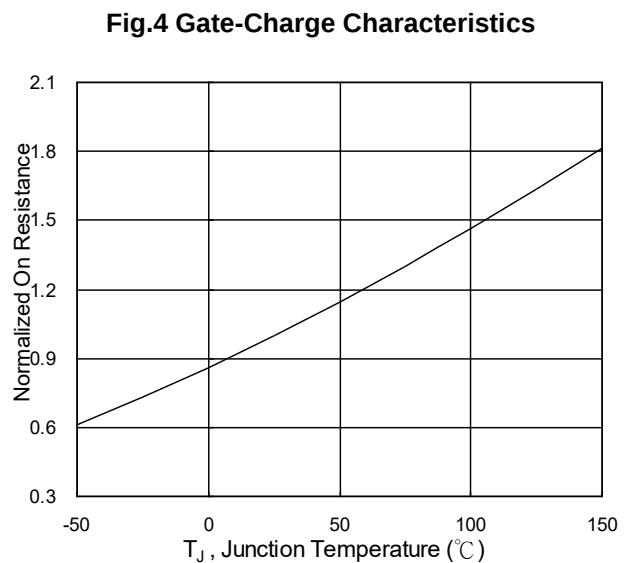
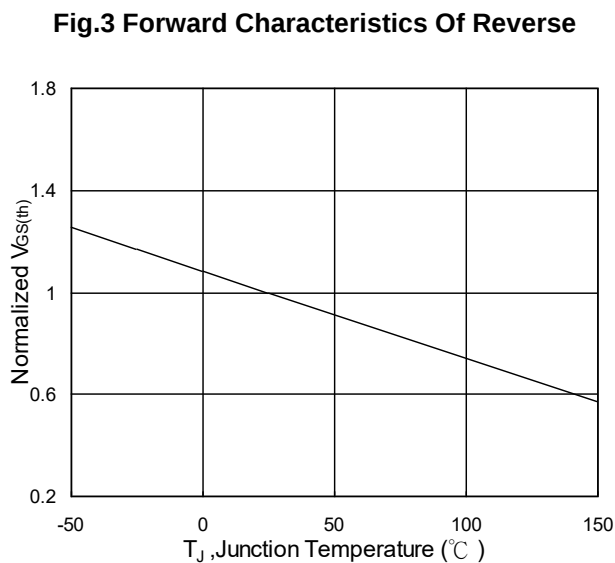
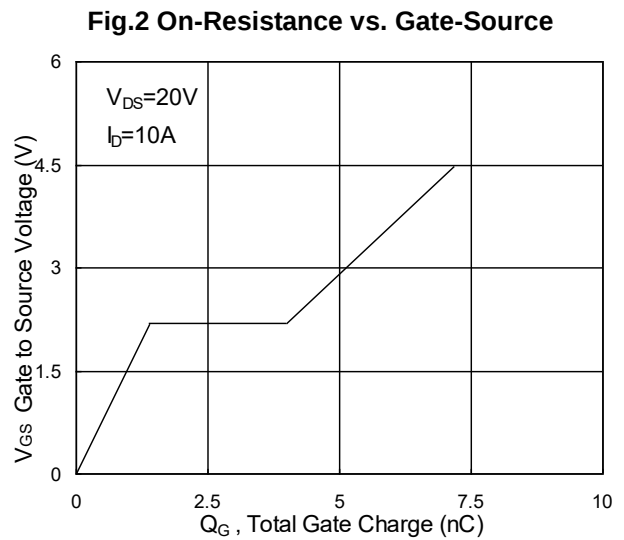
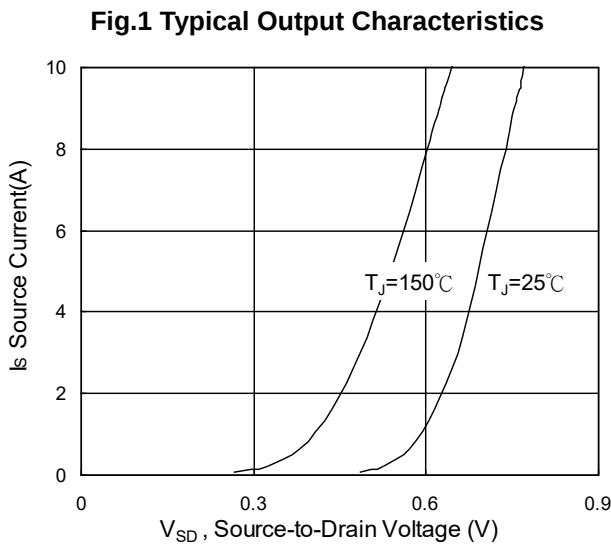
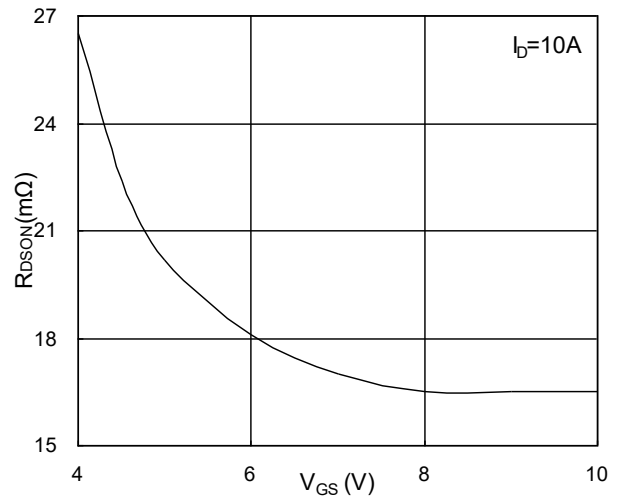
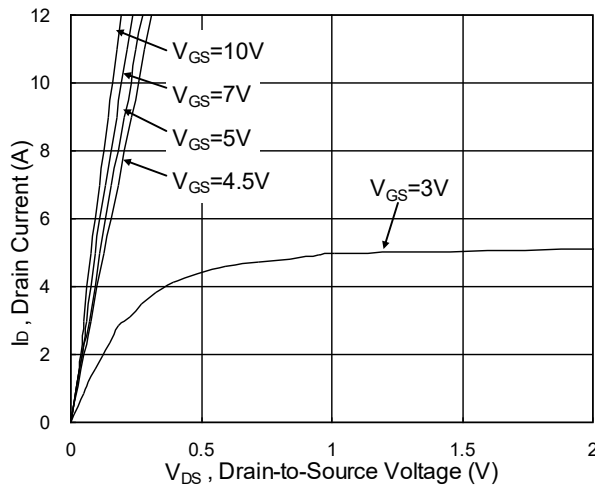
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.022	---	$V/^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=10A$	---	15	18	$\text{m}\Omega$
		$V_{GS}=4.5V$, $I_D=5A$	---	25	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.0	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.1	---	$\text{mV}/^{\circ}\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=24V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=10A$	---	4.5	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.5	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=20V$, $V_{GS}=4.5V$, $I_D=10A$	---	7.2	---	nC
Q_{gs}	Gate-Source Charge		---	1.4	---	
Q_{gd}	Gate-Drain Charge		---	2.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=12V$, $V_{GS}=10V$, $R_G=3.3\Omega$ $I_D=5A$	---	4.1	---	ns
T_r	Rise Time		---	9.8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	15.5	---	
T_f	Fall Time		---	6.0	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	572	---	pF
C_{oss}	Output Capacitance		---	81	---	
C_{rss}	Reverse Transfer Capacitance		---	65	---	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	28	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	56	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^{\circ}\text{C}$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.1\text{mH}$, $I_{AS}=21A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics



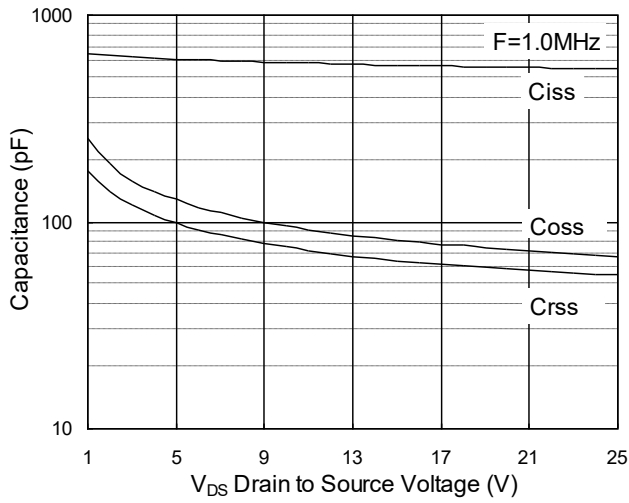


Fig.7 Capacitance

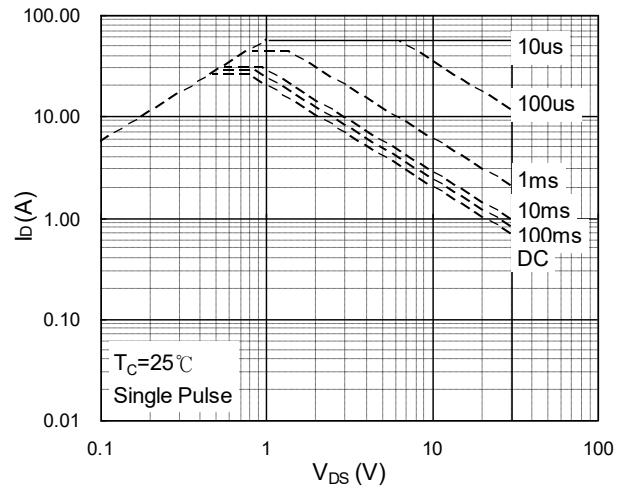


Fig.8 Safe Operating Area

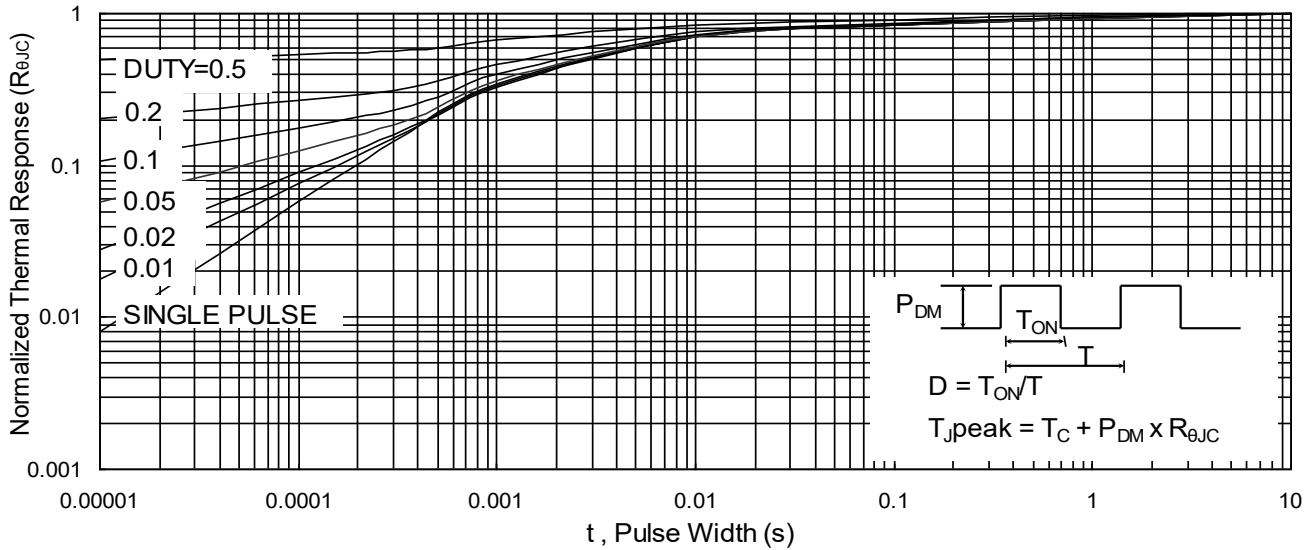


Fig.9 Normalized Maximum Transient Thermal Impedance

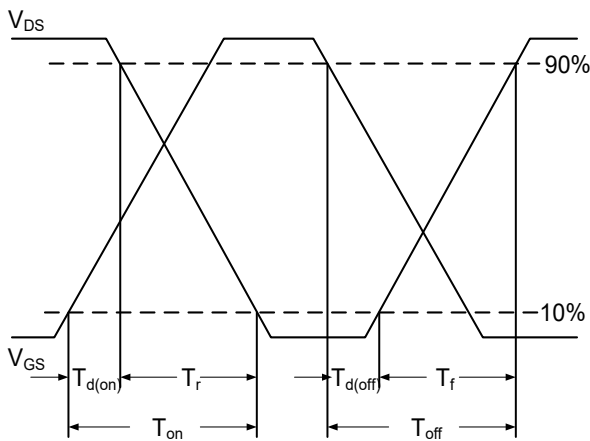


Fig.10 Switching Time Waveform

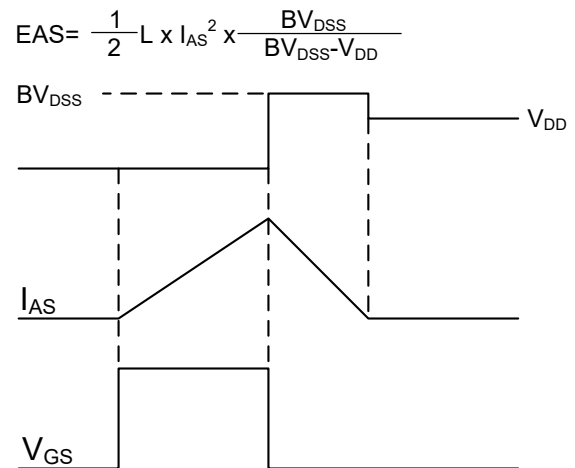
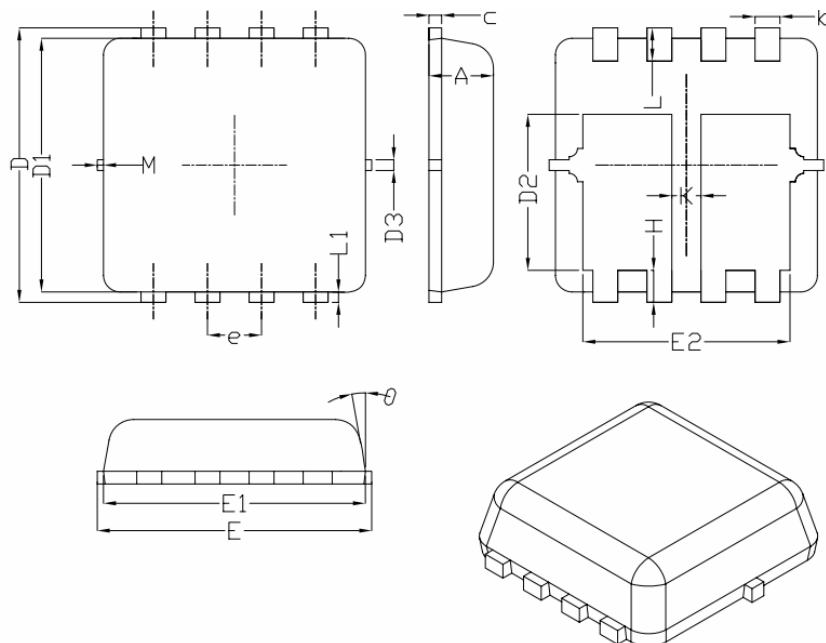


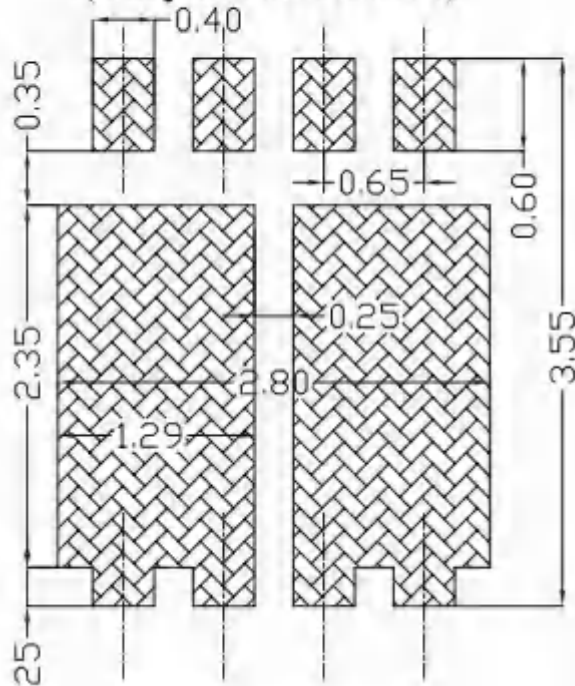
Fig.11 Unclamped Inductive Switching Waveform



DFN3X3B-8L(PowerPAK1212-8) Package Information



Land Pattern
(Only for Reference)



SYMBOL	DIMENSIONAL REOMTS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	---	0.13	---
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	---	0.13	---
K	0.30	---	---
θ	---	10°	12°
M	*	*	0.15
* Not specified			



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